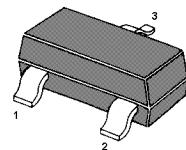


MMBT9014

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications

As complementary types the PNP
transistor MMBT9015 is recommended.



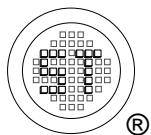
1.BASE 2.EMITTER 3.COLLECTOR
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	45	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{\text{CE}} = 5 \text{ V}$, $I_C = 1 \text{ mA}$ MMBT9014B MMBT9014C MMBT9014D	h_{FE}	110	220	-
	h_{FE}	200	450	-
	h_{FE}	420	800	-
Collector Base Cutoff Current at $V_{\text{CB}} = 50 \text{ V}$	I_{CBO}	-	50	nA
Emitter Base Cutoff Current at $V_{\text{EB}} = 5 \text{ V}$	I_{EBO}	-	50	nA
Collector Base Breakdown Voltage at $I_C = 100 \mu\text{A}$	$V_{(\text{BR})\text{CBO}}$	50	-	V
Collector Emitter Breakdown Voltage at $I_C = 1 \text{ mA}$	$V_{(\text{BR})\text{CEO}}$	45	-	V
Emitter Base Breakdown Voltage at $I_E = 100 \mu\text{A}$	$V_{(\text{BR})\text{EBO}}$	5	-	V
Collector Emitter Saturation Voltage at $I_C = 100 \text{ mA}$, $I_B = 10 \text{ mA}$	$V_{\text{CE}(\text{sat})}$	-	0.25	V
Base Emitter Saturation Voltage at $I_C = 100 \text{ mA}$, $I_B = 5 \text{ mA}$	$V_{\text{BE}(\text{sat})}$	-	1	V
Gain Bandwidth Product at $V_{\text{CE}} = 5 \text{ V}$, $I_C = 10 \text{ mA}$	f_T	100	-	MHz
Output Capacitance at $V_{\text{CB}} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{ob}	-	6	pF



MMBT9014

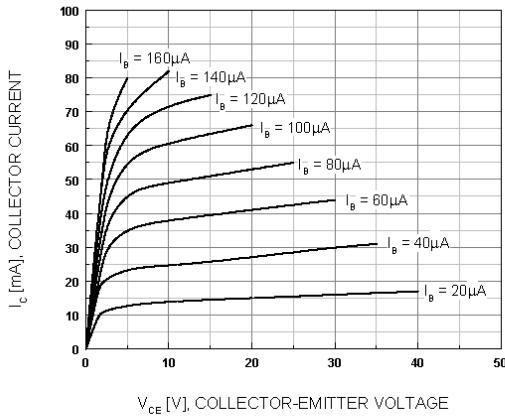


Figure 1. Static Characteristic

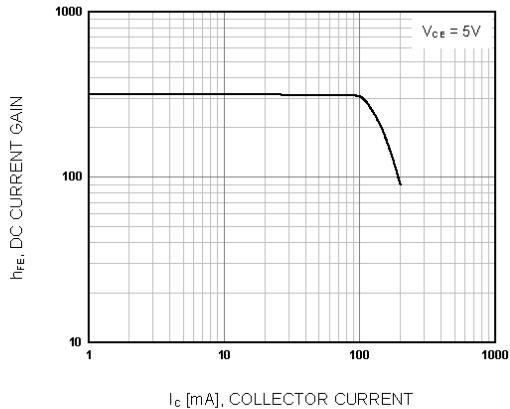
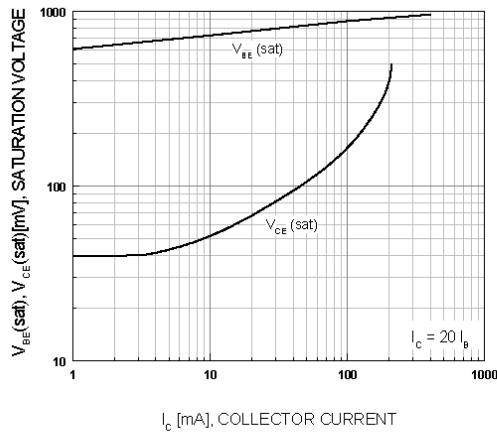


Figure 2. DC current Gain



**Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**

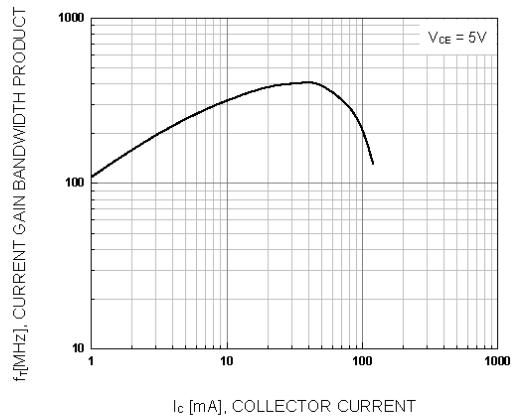


Figure 4. Current Gain Bandwidth Product

